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PATENT APPLICATION

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the application of:

KABASAWA

Art Unit: 2881

Application Number: 09/629,618

Examiner: B. Souw

Filed: July 31, 2000

Atty. Docket No.: 107443-00007

For: ION IMPLANTATION APPARATUS AND ION IMPLANTATION METHOD

AMENDMENT UNDER 37 C.F.R. § 1.111

Commissioner for Patents
Washington, D.C. 20231

November 5, 2002

Sir:

In reply to the Office Action mailed on July 5, 2002, the period for response being extended by the attached Petition for Extension of Time, please amend the above-identified application as follows:

IN THE SPECIFICATION

Please replace the Specification with the attached Substitute Specification.

IN THE CLAIMS

Please amend claims 1-24 as follows:

1. (Once Amended) An ion implantation apparatus for use in implanting an ion beam into a wafer by conducting the ion beam to the wafer along a predetermined path, the ion implantation apparatus comprising:

means for measuring, along the predetermined path, beam electric currents at a plurality of measurement positions different from each other;

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